

L Number	Hits	Search Text	DB	Time stamp
1	0	vcSEL and substrate near3 diffuse near3 reflect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 11:57
3	1	(substrate near3 diffuse near3 reflect\$3) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 11:57
2	177	substrate near3 diffuse near3 reflect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:16
4	693	substrate near3 pattern near3 reflect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:26
5	265	(substrate near3 pattern near3 reflect\$3) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:16
6	6	((substrate near3 pattern near3 reflect\$3) and laser) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:16
7	933	substrate and ((specular and diffuse) near3 reflect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:18
8	933	substrate and specular near3 reflect\$3 and diffuse near3 reflect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:18
9	6	(substrate and specular near3 reflect\$3 and diffuse near3 reflect\$3) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:20
10	5	(substrate and specular near3 reflect\$3 and diffuse near3 reflect\$3) and vcSEL	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:25
11	0	(substrate near3 pattern near3 reflect\$3) and vcSEL	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:25
12	6257	372/43.ccls. substrate near3 pattern near3 reflect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:26
13	1	372/43.ccls. and substrate near3 pattern near3 reflect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:26
14	0	372/98.ccls. and substrate near3 pattern near3 reflect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:27
15	35	372/98.ccls. and substrate near3 reflect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 12:29
16	114	372/43.ccls. and substrate near3 reflect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/06 13:21
17	1	"5814839".PN.	USPAT	2004/06/06 12:45
18	0	6545296.URPN.	USPAT	2004/06/06 12:46

19	288	vcSEL and optical near3 communication\$1 and high near3 power	USPAT; US-PGPUB	2004/06/06 13:22
20	126	(vcSEL and optical near3 communication\$1 and high near3 power) and 372/\$.ccls.	USPAT; US-PGPUB	2004/06/06 13:23
-	71	438/\$.ccls. and etch\$3 and photoelectrochemical	USPAT; US-PGPUB	2003/08/18 10:16
-	3	(438/\$.ccls. and etch\$3 and photoelectrochemical) and vcSEL	USPAT; US-PGPUB	2003/07/28 07:22
-	50	(438/\$.ccls. and etch\$3 and photoelectrochemical) and condition\$3	USPAT; US-PGPUB	2003/07/28 07:23
-	2	((438/\$.ccls. and etch\$3 and photoelectrochemical) and condition\$3) and vcSEL	USPAT; US-PGPUB	2003/07/28 07:23
-	13	vcSEL and (specular near3 reflect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 17:23
-	360	(reduc\$4 near3 (specular near3 reflect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:54
-	2	((reduc\$4 near3 (specular near3 reflect\$3))) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:42
-	10	((reduc\$4 near3 (specular near3 reflect\$3))) and (semiconductor near3 laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:41
-	210	(low\$3 near3 (specular near3 reflect\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:41
-	2	((low\$3 near3 (specular near3 reflect\$4))) and (semiconductor near3 laser\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:42
-	0	((low\$3 near3 (specular near3 reflect\$4))) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:42
-	97	((low\$3 near3 (specular near3 reflect\$4))) and substrate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:43
-	162	((reduc\$4 near3 (specular near3 reflect\$3))) and substrate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:43
-	56	((((reduc\$4 near3 (specular near3 reflect\$3))) and substrate\$1) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:43
-	1	((zero near3 order near3 (specular near3 reflect\$3))) and vcSEL	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:57
-	48	(grating near3 substrate) and vcSEL	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 10:58
-	0	(zero near3 order near3 (vcSEL))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 11:08
-	44	(zero near3 order near3 (specular near3 reflect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 11:42

-	0	vcSEL and dbr and (substrate near3 low near3 reflect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 11:51
-	112	vcSEL and dbr and (substrate near3 reflect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 12:06
-	88	(vcSEL and dbr and (substrate near3 reflect\$3)) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 11:53
-	0	substrate near3 antireflect\$3 near3 feature\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 11:55
-	1423	substrate near3 antireflect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 11:55
-	0	(substrate near3 antireflect\$3) and vcSEL and dbr	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 11:55
-	12	(substrate near3 antireflect\$3) and dbr	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 11:56
-	533	(vcSEL or (surface near3 emit\$4)) and (specular near3 reflect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 12:06
-	1	(substrate near3 antireflect\$3) and ((vcSEL or (surface near3 emit\$4)) and (specular near3 reflect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 11:58
-	6	(vcSEL and dbr and (substrate near3 reflect\$3)) and ((vcSEL or (surface near3 emit\$4)) and (specular near3 reflect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 12:01
-	70	(vcSEL or (surface near3 emit\$4)) and (specular near3 reflect\$3) and (substrate near3 reflect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 12:41
-	6	vcSEL and dbr and (glare or (specular near3 reflect\$3)) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 12:42
-	1	"6417901".PN.	USPAT	2003/08/18 12:46
-	1	"6233264".PN.	USPAT	2003/08/18 12:46
-	1	"5810925".PN.	USPAT	2003/08/18 12:47
-	1	"5679152".PN.	USPAT	2003/08/18 12:47
-	5	(substrate near3 scat\$7) AND (VCSEL OR (SURFACE NEAR3 emitting)) and dbr	USPAT; US-PGPUB	2003/08/18 12:50
-	5	(substrate near3 scat\$7) AND (VCSEL OR (SURFACE NEAR3 emitting)) and dbr	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 12:58
-	1029	(VCSEL OR (SURFACE NEAR3 emitting)) and dbr	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 13:02
-	7	((VCSEL OR (SURFACE NEAR3 emitting)) and dbr) and (glare or (specular near3 reflect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 13:00

-	2	((VCSEL OR (SURFACE NEAR3 emitting)) and dbr) and (substrate near3 antireflect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 13:01
-	934	(VCSEL OR (SURFACE NEAR3 emitting)) and dbr and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 13:03
-	881	((VCSEL OR (SURFACE NEAR3 emitting)) and dbr and substrate) and reflect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 13:04
-	520	((VCSEL OR (SURFACE NEAR3 emitting)) and dbr and substrate) and reflect\$4) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 13:04
-	122	((VCSEL OR (SURFACE NEAR3 emitting)) and dbr and substrate) and reflect\$4) and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 13:04
-	180	(pattern\$3 near3 substrate) and vcsel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 13:51
-	0	((pattern\$3 near3 substrate) and vcsel) and reflect\$4 and (specular or diffuse\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 13:53
-	153	((pattern\$3 near3 substrate) and vcsel) and reflect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 14:21
-	295	vcsel and diffuse\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 14:21
-	108	vcsel and diffuse\$1 and dbr and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 14:21
-	55	vcsel and (reflect\$4 near3 (diffuse\$1 or scatter\$3)) and dbr and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 14:25
-	265	vcsel and dbr and substrate	USPAT	2003/08/18 14:25
-	197	(vcsel and dbr and substrate) and 372/\$.ccls.	USPAT	2003/08/18 14:26
-	47	(vcsel and dbr and substrate) and 438/\$.ccls.	USPAT	2003/08/18 14:28
-	5	vcsel and dbr and ((grat\$3 or step) near substrate)	USPAT	2003/08/18 14:32
-	0	vcsel and dbr and ((grat\$3) near substrate)	USPAT	2003/08/18 14:32
-	2	vcsel and dbr and ((grat\$3) near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 14:33
-	1	(antireflection near grating) and substrate and dbr	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 14:35
-	6	(antireflection near grating) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 14:39
-	4106	((specular near3 reflection) or glare) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 14:41

-	11	((specular near3 reflection) or glare) and substrate) and vcsel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 14:41
-	1782	specular and scattering and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:07
-	10	(specular and scattering and substrate) and vcsel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 14:53
-	121	specular and scattering and ((textured or rough\$4) near3 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:27
-	0	(specular and scattering and ((textured or rough\$4) near3 substrate)) and vcsel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:09
-	121	(specular and scattering and ((textured or rough\$4) near3 substrate)) and (vcsel or (surface emitting))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:09
-	72	(semiconductor near3 laser) and (semiconductor near3 substrate) and specular and reflect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:38
-	138	(semiconductor near3 substrate) and (specular near reflect\$4) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:39
-	5	((semiconductor near3 substrate) and (specular near reflect\$4) and laser) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:40
-	24	((semiconductor near3 substrate) and (specular near reflect\$4) and laser) and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:43
-	127	vcsel and dbr and substrate and scattering	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:45
-	7	vcsel and dbr and substrate and specular	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:45
-	13	(vcsel and dbr and substrate and scattering) and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:46
-	55	(vcsel and dbr and substrate and scattering) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:52
-	33	substrate near specular near reflect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:52
-	0	(substrate near specular near reflect\$4) and vcsel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:53
-	0	(substrate near specular near reflect\$4) and surface near emitting near laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 15:53

-	1	vcSEL and giro and grating and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 16:10
-	0	vcSEL and specular and duffuse	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 16:10
-	8	vcSEL and specular and diffuse	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 16:10
-	14	(substrate near grating) and specular and diffuse	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 16:12
-	77	(semiconductor near laser) and specular and diffuse	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 16:13
-	71	(semiconductor near laser) and specular and diffuse and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 16:13
-	1	"6417901".PN.	USPAT	2003/08/18 16:32
-	1	"6233264".PN.	USPAT	2003/08/18 16:32
-	1	"5679152".PN.	USPAT	2003/08/18 16:33
-	1	"5810925".PN.	USPAT	2003/08/18 16:33
-	2229	(semiconductor near3 laser) and (pattern\$3 near3 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 16:37
-	208	((semiconductor near3 laser) and (pattern\$3 near3 substrate)) and ((anti adj reflect\$3) or antireflect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 16:38
-	18	((semiconductor near3 laser) and (pattern\$3 near3 substrate)) and ((anti adj reflect\$3) or antireflect\$3)) and specula\$5 and diffus\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 16:40
-	643	vcSEL and (scattering or diffus\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 17:26
-	209	(vcSEL and (scattering or diffus\$3)) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 17:24
-	117	vcSEL and ((scattering or diffus\$3) near3 (rays or beam))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 17:25
-	23	(vcSEL and ((scattering or diffus\$3) near3 (rays or beam))) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 17:27
-	226	vcSEL and (scattering or diffus\$3) and dbr	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 17:26
-	123	(vcSEL and (scattering or diffus\$3) and dbr) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 17:27
-	0	subwavelength near substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 17:40

-	12	subwavelength near structure	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 18:04
-	4	vcSEL near3 leak\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 18:06
-	2	vcSEL and dbr and (grating near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 18:09
-	177	vcSEL and dbr and (grating and substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 18:09
-	78	vcSEL and dbr and grating and substrate and (specular or diffus\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/18 18:10
-	1	"6301281".PN.	USPAT	2003/08/18 18:19
-	1	"6031243".PN.	USPAT	2003/08/18 18:19
-	1	"6002705".PN.	USPAT	2003/08/18 18:19
-	1	"5995531".PN.	USPAT	2003/08/18 18:19
-	8	(surface near3 texture\$1) and vcSEL	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/19 14:59
-	0	(antireflect\$3 near3 layer) and vcSEL and substrate and dbr	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/19 15:01
-	15	(antireflect\$3 near3 layer) and vcSEL	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/19 15:05
-	144	(edge near emitting near laser) and vcSEL and dbr and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/19 15:06
-	165	led and vcSEL and dbr and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/19 15:07